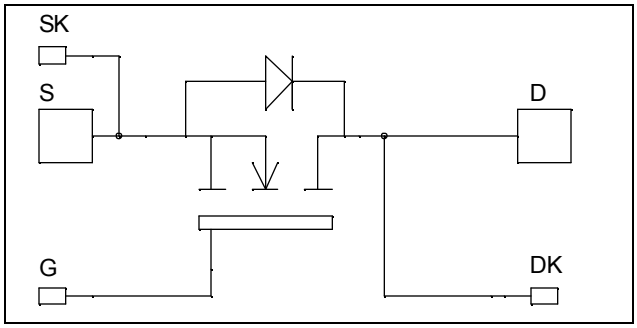
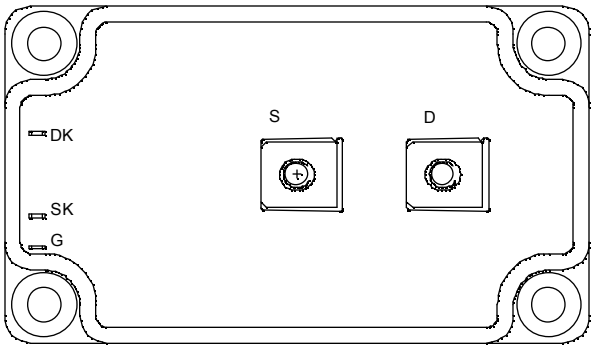
APTM120UM70FAG

Single switch MOSFET Power Module

V_{DSS} = 1200V
R_{DSon} = 70mΩ typ @ Tj = 25°C
I_D = 171A @ Tc = 25°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7® FREDFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		1200	V
I_D	Continuous Drain Current	T_c = 25°C	171	A
		T_c = 80°C	126	
I_{DM}	Pulsed Drain current		684	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		80	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	5000	W
I_{AR}	Avalanche current (repetitive and non repetitive)		24	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		3200	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 1200V	T_j = 25°C			1.5	mA
		V_{GS} = 0V, V_{DS} = 1000V	T_j = 125°C			6	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 85.5A			70	80	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 30mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		43.5		nF
C_{oss}	Output Capacitance			6.6		
C_{rss}	Reverse Transfer Capacitance			1.2		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 600V I_D = 171A		1650		nC
Q_{gs}	Gate – Source Charge			192		
Q_{gd}	Gate – Drain Charge			1074		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 800V I_D = 171A R_G = 0.8Ω		20		ns
T_r	Rise Time			17		
$T_{d(off)}$	Turn-off Delay Time			245		
T_f	Fall Time			62		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 800V I_D = 171A, R_G = 0.8Ω		7.6		mJ
E_{off}	Turn-off Switching Energy			6.9		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 800V I_D = 171A, R_G = 0.8Ω		13.8		mJ
E_{off}	Turn-off Switching Energy			8.5		

Source - Drain diode ratings and characteristics

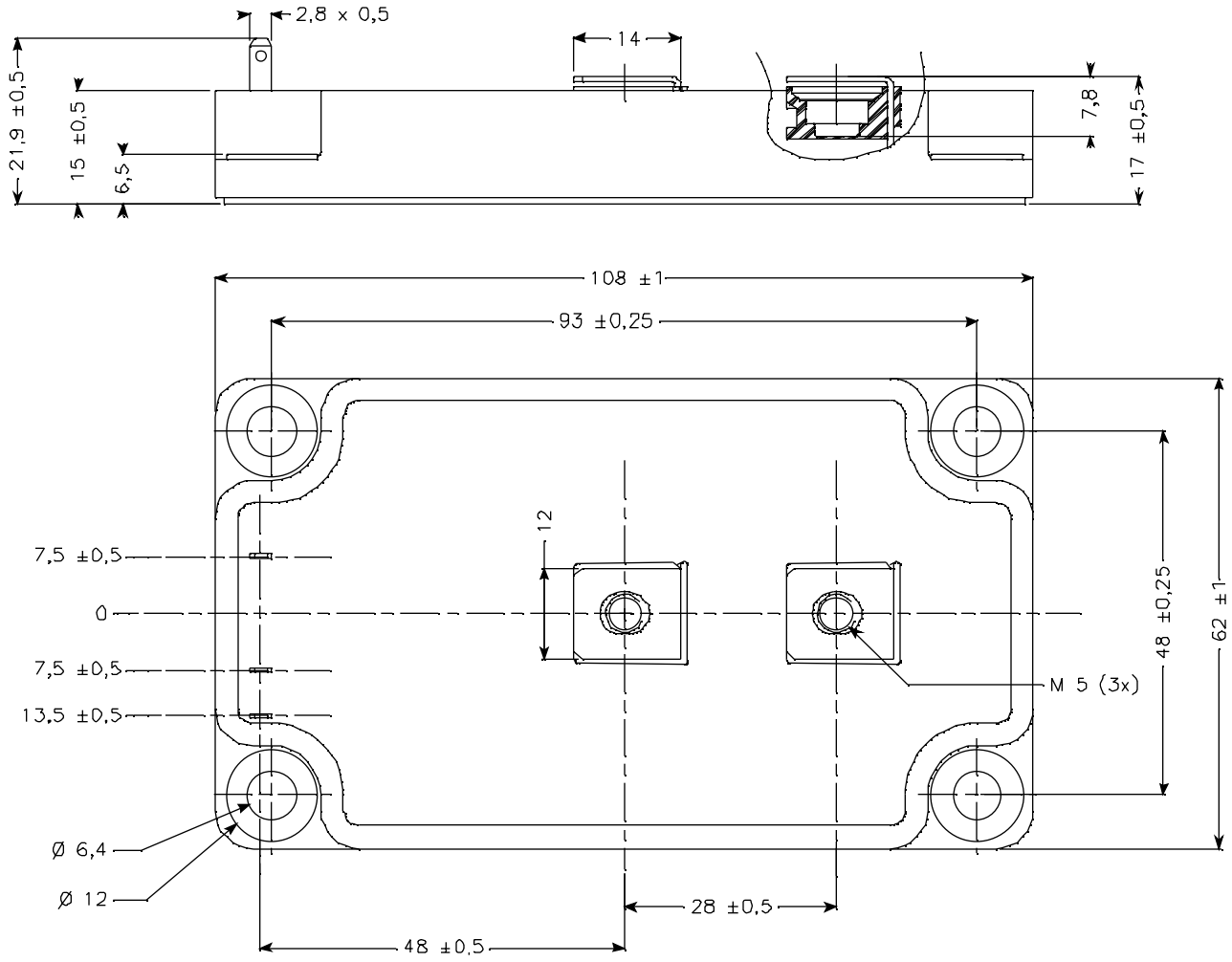
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)		Tc = 25°C			171	A
			Tc = 80°C			126	
V_{SD}	Diode Forward Voltage	V_{GS} = 0V, I_S = - 171A				1.3	V
dv/dt	Peak Diode Recovery ❶					18	V/ns
t_{rr}	Reverse Recovery Time	I_S = - 171A V_R = 600V di_S/dt = 600A/µs	T_j = 25°C			375	ns
			T_j = 125°C			860	
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		12		µC
			T_j = 125°C		54		

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.
$I_S \le$ - 171A di/dt ≤ 700A/µs $V_R \le V_{DSS}$ $T_j \le$ 150°C

Thermal and package characteristics

Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance					0.025	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					280	g

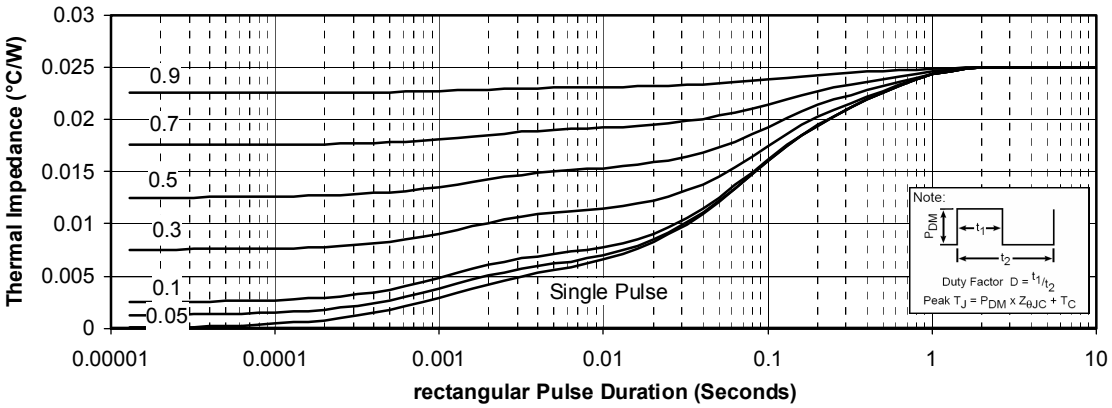
SP6 Package outline (dimensions in mm)



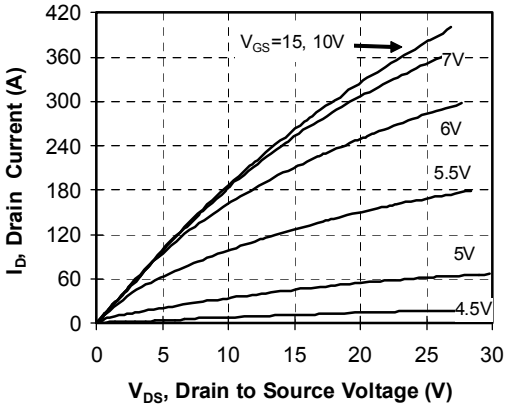
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve

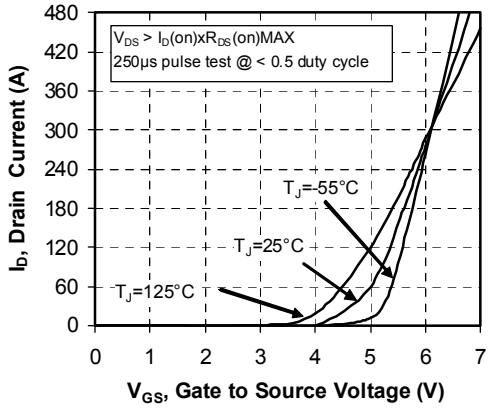
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



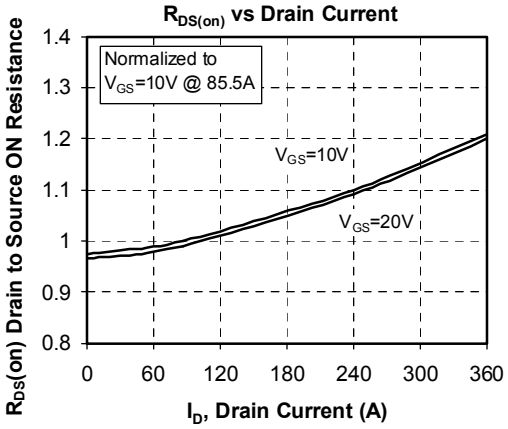
Low Voltage Output Characteristics



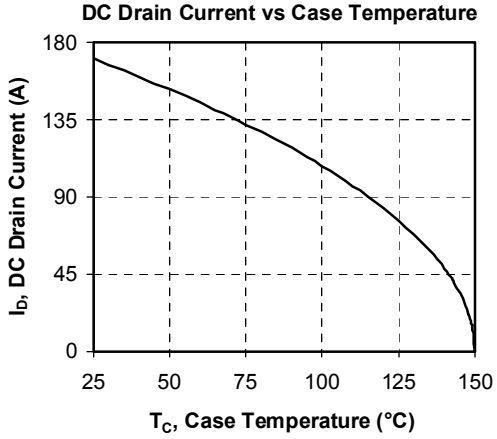
Transfert Characteristics



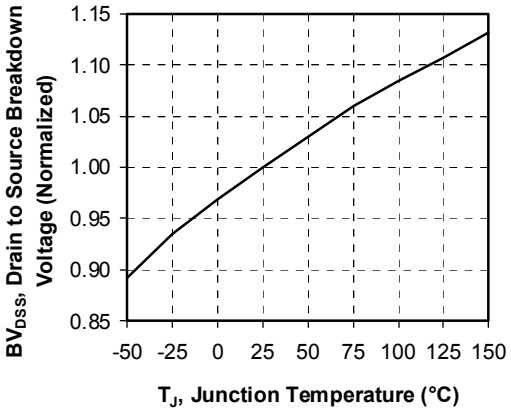
$R_{DS(on)}$ vs Drain Current



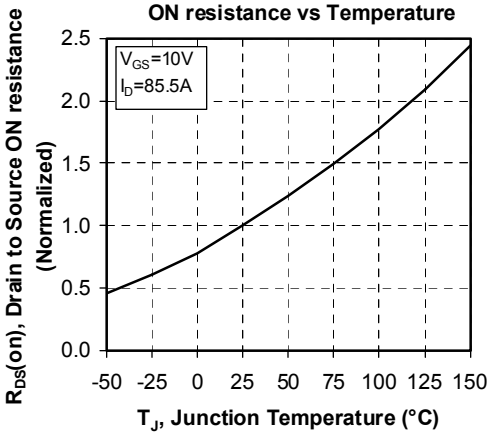
DC Drain Current vs Case Temperature



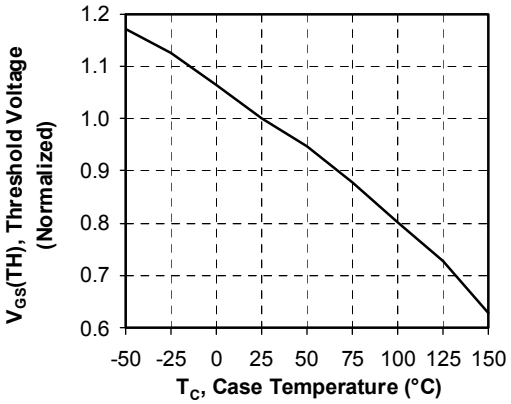
Breakdown Voltage vs Temperature



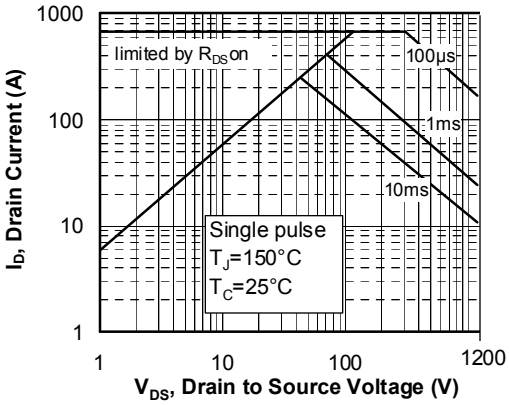
ON resistance vs Temperature



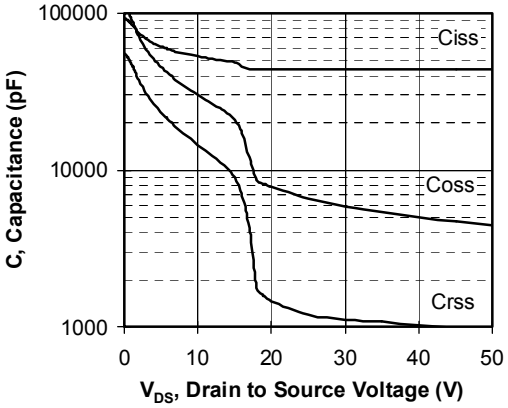
Threshold Voltage vs Temperature



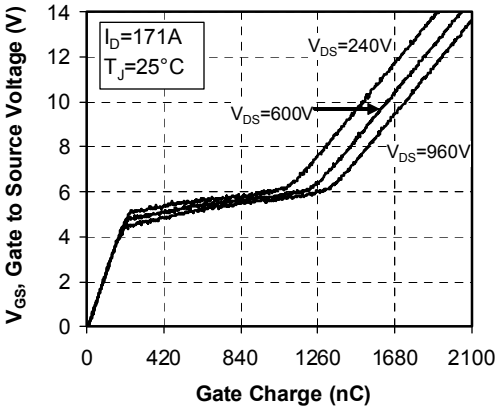
Maximum Safe Operating Area



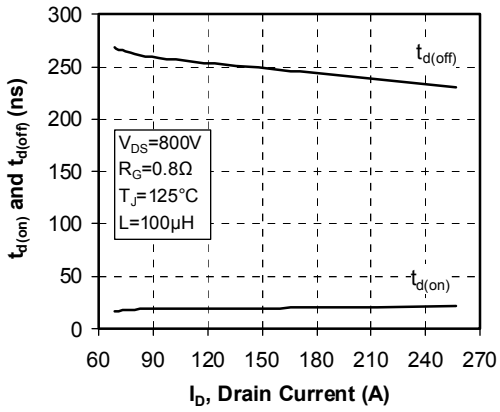
Capacitance vs Drain to Source Voltage



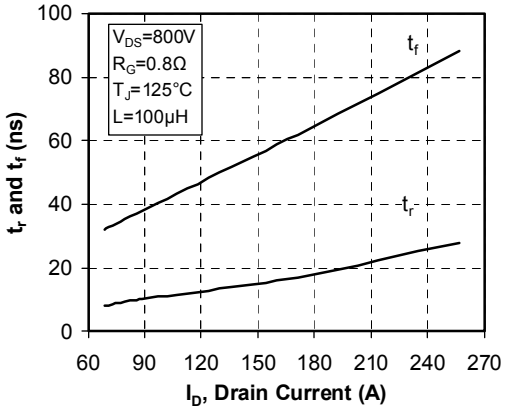
Gate Charge vs Gate to Source Voltage



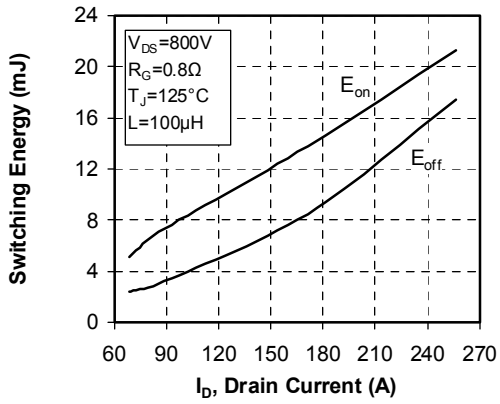
Delay Times vs Current



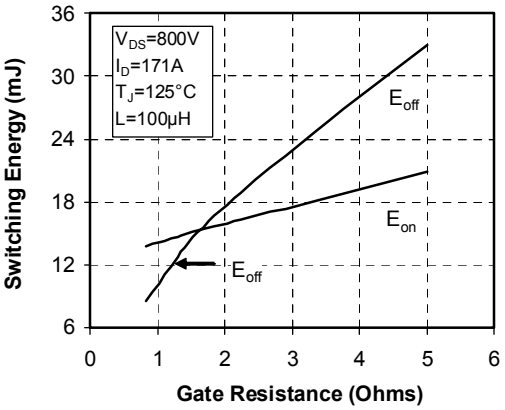
Rise and Fall times vs Current



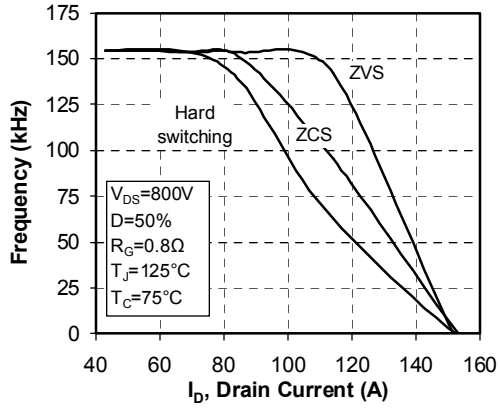
Switching Energy vs Current



Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage